NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

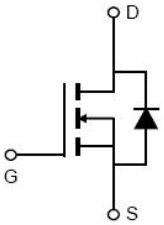
General Features

- V_{DS} =85V,I_D =150A
  $R_{DS(ON)}$=3.7mΩ , typical @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!

100% ΔVds TESTED!

TO-220



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP045N85	NCEP045N85	TO-220	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	150	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	106	A
Pulsed Drain Current	I_{DM}	600	A
Maximum Power Dissipation	P_D	198	W
Derating factor		1.32	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	870	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.76	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	85		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=85V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	3.7	4.5	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=40A		70	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=40V,V_{GS}=0V, F=1.0MHz	-	3600	-	PF
Output Capacitance	C_{oss}		-	775	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=40V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	21	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	54	-	nS
Turn-Off Fall Time	t_f		-	15	-	nS
Total Gate Charge	Q_g	V_{DS}=40V,I_D=20A, V_{GS}=10V	-	61	-	nC
Gate-Source Charge	Q_{gs}		-	17		nC
Gate-Drain Charge	Q_{gd}		-	16.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-		1.2	V
Diode Forward Current	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =75A di/dt = 100A/μs	-	72	-	nS
Reverse Recovery Charge	Qrr		-	110	-	nC

Notes:

1. EAS condition : Tj=25℃,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

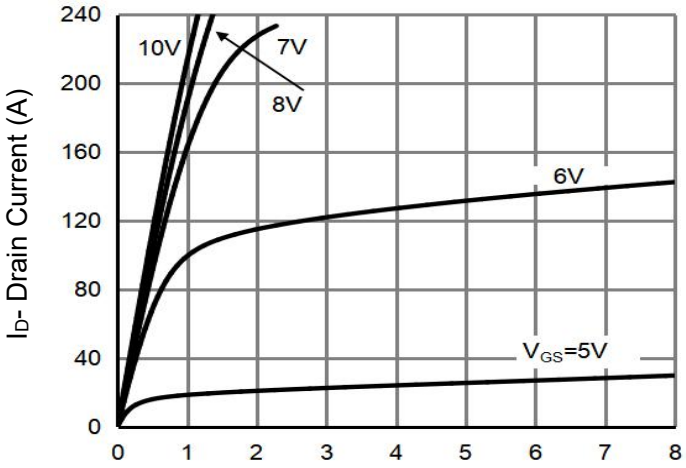


Figure 1 Output Characteristics

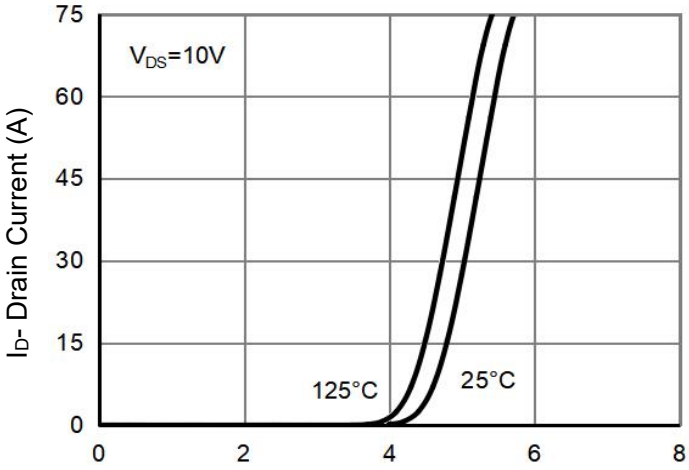


Figure 2 Transfer Characteristics

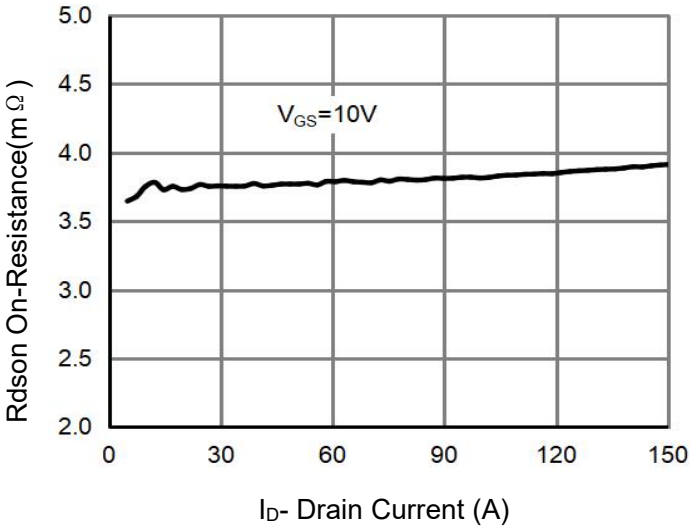


Figure 3 Rdson- Drain Current

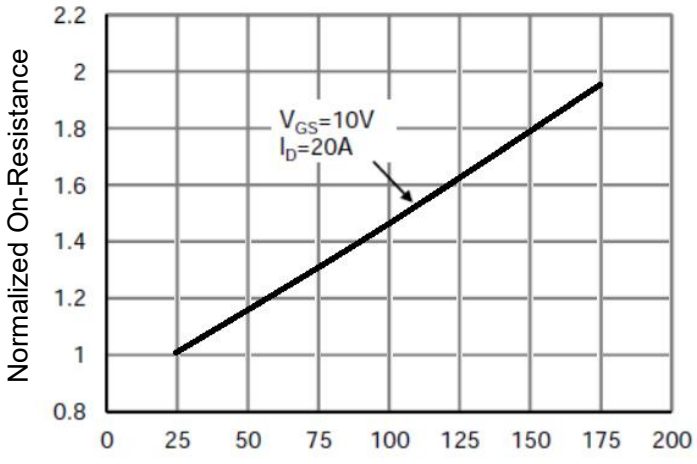


Figure 4 Rdson-Junction Temperature

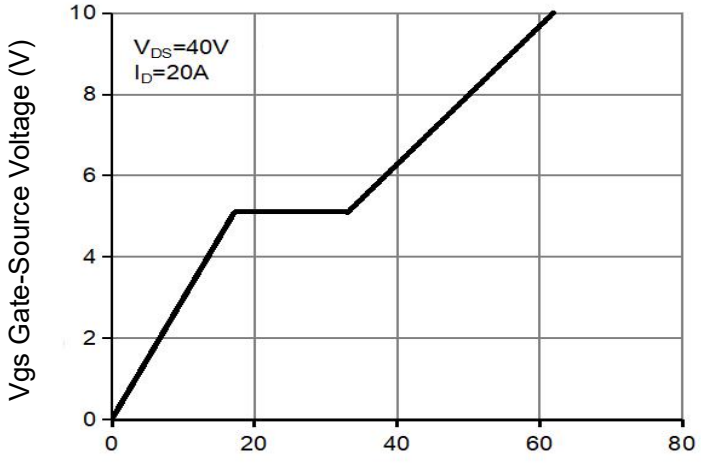


Figure 5 Gate Charge

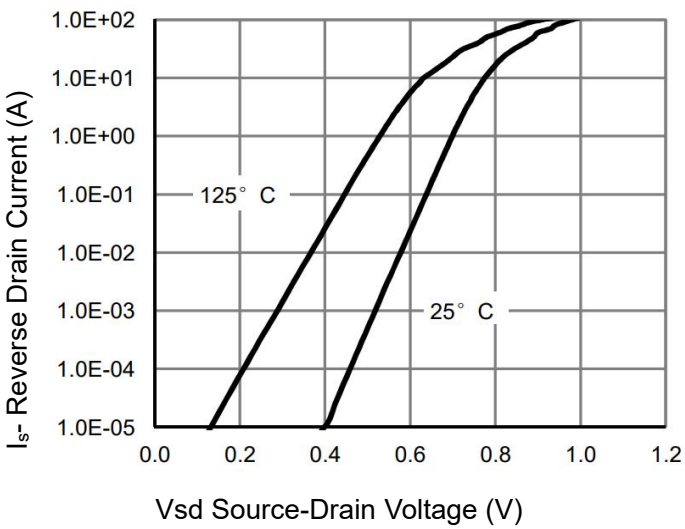


Figure 6 Source- Drain Diode Forward

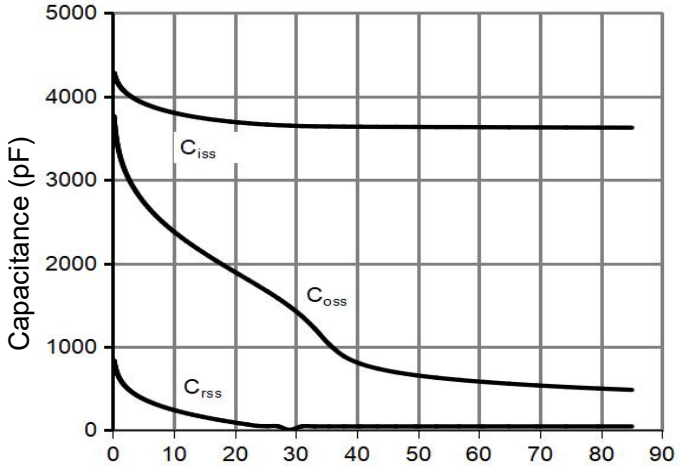


Figure 7 Capacitance vs Vds

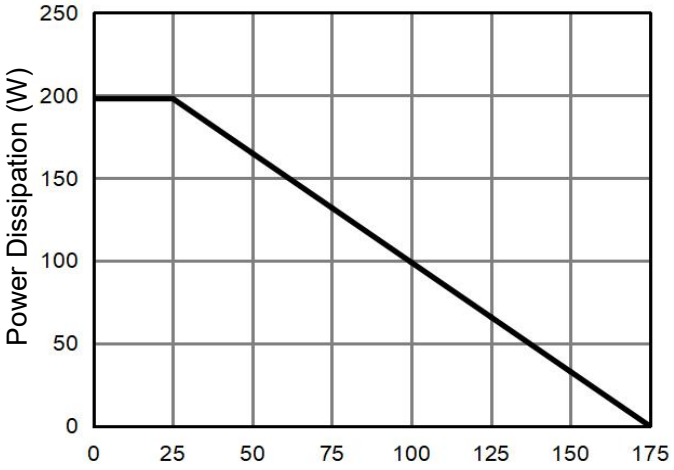


Figure 9 Power De-rating

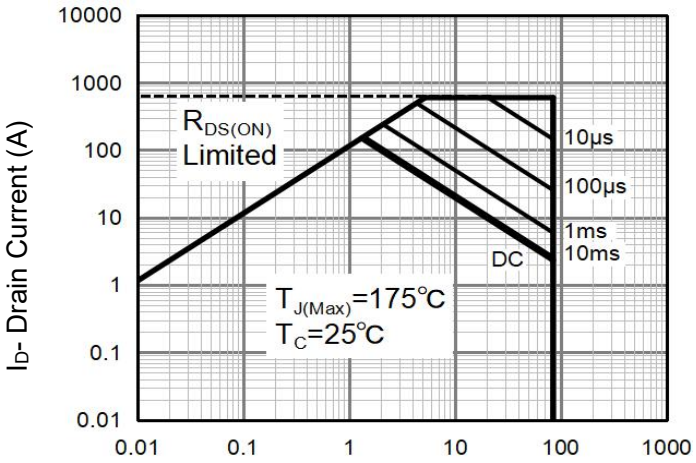


Figure 8 Safe Operation Area (Note3)

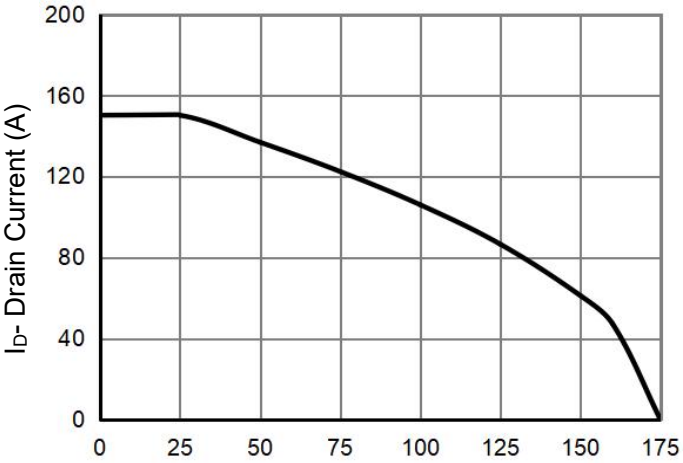


Figure 10 Current De-rating

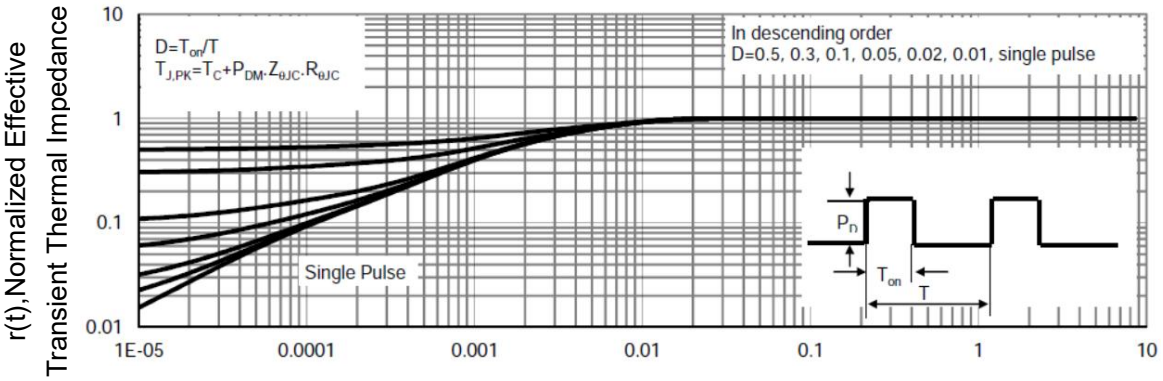
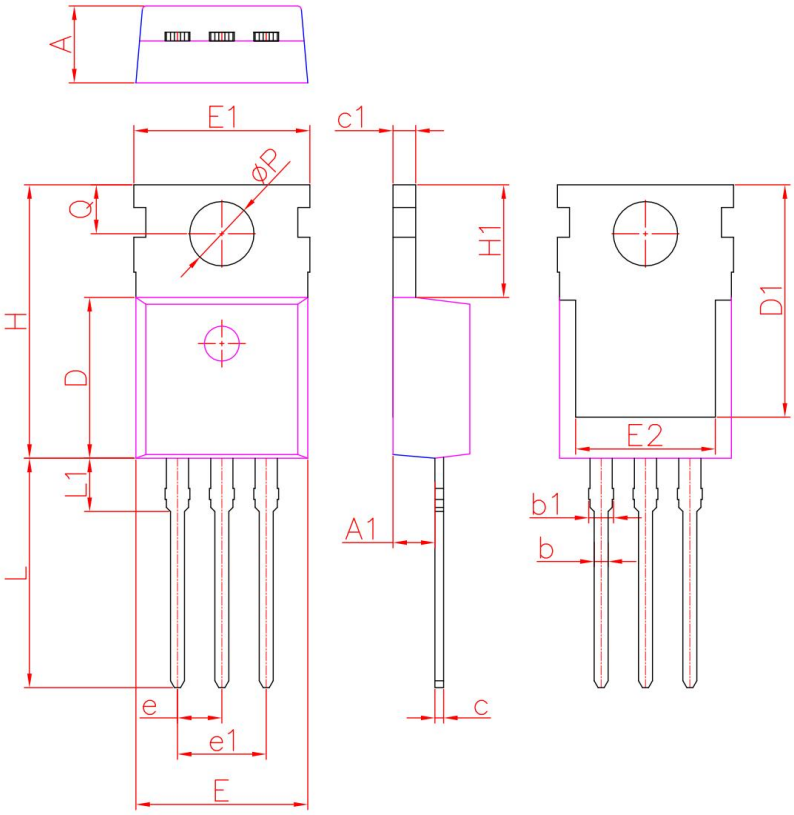


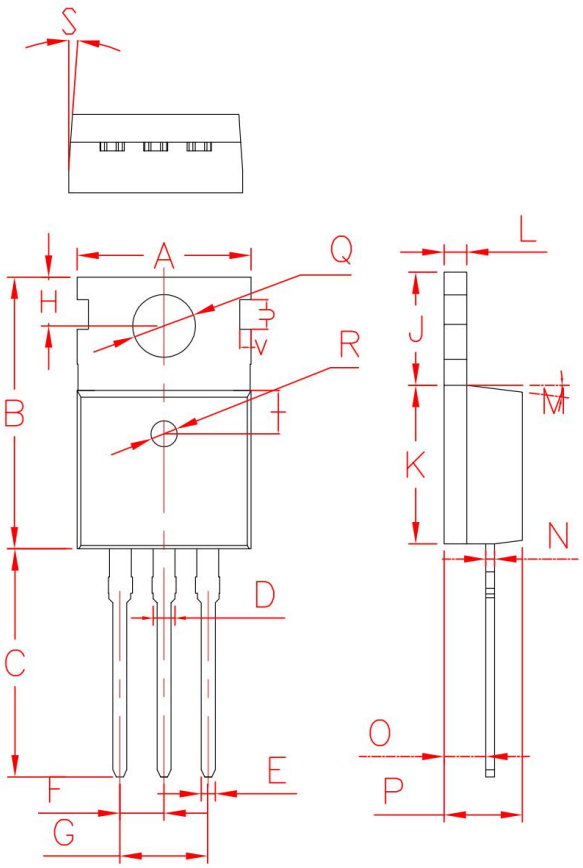
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L(E) Package Information



TO220			
DIM.	MIN.	NOM.	MAX.
A	4.20	4.40	4.60
A1	2.25	2.40	2.55
b	0.70	0.80	0.90
b1	1.17	1.27	1.37
c	0.33	0.50	0.65
c1	1.20	1.30	1.40
D	8.95	9.20	9.75
D1	13.10	13.30	13.50
E	9.74	9.84	10.04
E1	9.91	10.08	10.25
E2	7.90	8.00	8.10
e	2.54BSC		
e1	5.08BSC		
H	15.45	15.65	15.85
H1	6.30	6.45	6.60
L	12.90	13.13	13.40
L1	2.85	3.05	3.25
Q	2.65	2.80	2.95
øP	3.40	3.68	3.80
All dimensions in millimeters			

TO-220-3L(S) Package Information



Symbol	Min	Non	Max
A	9.80	10.00	10.20
B	15.40	15.60	15.80
C	12.75	13.10	13.45
D	1.18	1.31	1.44
E	0.70	0.80	0.90
F	2.42	2.54	2.66
G	4.84	5.08	5.32
H	2.73	2.80	2.87
I	2.40	2.50	2.60
J	6.40	6.50	6.60
K	9.00	9.10	9.20
L	1.29	1.30	1.32
M	6.5°	7.0°	7.5°
N	0.48	0.50	0.56
O	2.35	2.4	2.5
P	4.4	4.5	4.7
Q	3.5	3.6	3.63
R	1.4	1.5	1.6
S	2°	2.5°	3°
U	1.65	1.75	1.85
V	0.58	0.68	0.78

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